

L Number	Hits	Search Text	DB	Time stamp
1	2522	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:44
2	10815	black near2 matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:44
3	142802	silicon near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:49
7	39943	(cmp or (chemical adj mechanical)near2 polishing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:50
9	0	((silicon near2 substrate) near ((cmp or (chemical adj mechanical)near2 polishing))) and (black near2 matrix)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:50
10	0	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.) and ((silicon near2 substrate) near ((cmp or (chemical adj mechanical)near2 polishing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:51
8	54	(silicon near2 substrate) near ((cmp or (chemical adj mechanical)near2 polishing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:53
11	1622	(tft or (thin adj film adj transistor) or transistor) near panel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:54
12	0	((silicon near2 substrate) near ((cmp or (chemical adj mechanical)near2 polishing))) and ((tft or (thin adj film adj transistor) or transistor) near panel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 16:54
-	25220	(tft or (thin adj film adj transistor) with panel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 11:31
-	2682	((tft or (thin adj film adj transistor) with panel)) with transparent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 11:32
-	73	((tft or (thin adj film adj transistor) with panel)) with transparent) with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 11:32
-	45	((tft or (thin adj film adj transistor) with panel)) with transparent) with insulator) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 11:41
-	4	((transparent adj substrate) with (silicon adj substrate)) with tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 11:42

-	102	(transparent adj substrate) with (silicon adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 15:55
-	0	(( thin adj film adj transistor adj panel)) with ((transparent adj substrate) with (silicon adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:01
-	0	(( thin adj film adj transistor adj panel)) and((transparent adj substrate) with (silicon adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:12
-	0	(( thin adj film adj transistor adj panel)) with ((transparent adj substrate) and (silicon adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:10
-	213	( thin adj film adj transistor adj panel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:11
-	0	(( thin adj film adj transistor adj panel)) and((transparent and silicon) adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:13
-	1	(( thin adj film adj transistor adj panel)) with (transparent and silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:14
-	0	(( thin adj film adj transistor adj panel)) with (transparent and (silicon adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:14
-	0	(( thin adj film adj transistor adj panel)) and(transparent and (silicon adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:14
-	0	(( thin adj film adj transistor adj panel)) with (silicon adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:15
-	31	(( thin adj film adj transistor adj panel)) with transparent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 13:15
-	52	(transparent adj substrate) with (silicon adj substrate) and remove\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 15:56
-	19	(transparent adj substrate) with (silicon adj substrate) same remove\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 16:01
-	16235	(silicon adj substrate) same remove\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/10 16:02

-	14	((silicon adj substrate) same remove\$3) same transparent) same insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/10 16:02
-	162	((silicon adj substrate) same remove\$3) same transparent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/10 16:08
-	1	"6252300".PN.	USPAT; US-PGPUB	2002/07/10 16:11
-	1	"5985693".PN.	USPAT; US-PGPUB	2002/07/10 16:11
-	1	"5923067".PN.	USPAT; US-PGPUB	2002/07/10 16:12
-	1	"5880010".PN.	USPAT; US-PGPUB	2002/07/10 16:12
-	1	"5426072".PN.	USPAT; US-PGPUB	2002/07/10 16:13
-	2121	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.	USPAT; US-PGPUB	2003/11/13 16:43
-	0	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.	EPO; JPO; DERWENT; IBM TDB	2003/04/02 11:11
-	335508	bond	USPAT; US-PGPUB	2003/04/02 11:27
-	128580	silicon same substrate	USPAT; US-PGPUB	2003/04/02 11:28
-	7737	black with matrix	USPAT; US-PGPUB	2003/04/02 11:29
-	451	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.) and bond	USPAT; US-PGPUB	2003/04/02 11:29
-	397	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.) and bond) and (silicon same substrate)	USPAT; US-PGPUB	2003/04/02 11:29
-	32	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.) and bond) and (silicon same substrate)) and (black with matrix)	USPAT; US-PGPUB	2003/04/02 11:37
-	10	("5008218"   "5468521"   "5527649"   "5589962"   "5693541"   "5747121"   "5767930"   "5807772"   "5888839"   "5926735").PN.	USPAT	2003/04/02 11:34
-	2	6127199.URPN.	USPAT	2003/04/02 11:35
-	805814	remove	USPAT; US-PGPUB	2003/04/02 11:37
-	10558	remove same (silicon same substrate)	USPAT; US-PGPUB	2003/04/02 11:37
-	188	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.) and (remove same (silicon same substrate))	USPAT; US-PGPUB	2003/04/02 11:38
-	8	((438/29) or (438/30) or (438/149) or (438/151) or (438/152)).CCLS.) and (remove same (silicon same substrate))) and (black with matrix)	USPAT; US-PGPUB	2003/04/02 11:38